PHPT61010NY

100 V, 10 A NPN high power bipolar transistor 20 March 2015

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61010PY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- · Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	10	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	20	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 10 A; I_B = 1 A; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	-	25	37	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В
3	Е	emitter	[d	, M
4	В	base	و ق ق ق	E sym123
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	- Sylli123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61010NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61010NY	1010NAB

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

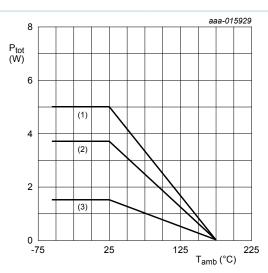
Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	100	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	10	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	20	Α
I _B	base current			-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			<u>[4]</u>	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².

^[3] Device mounted on an ceramic PCB; Al₂O₃, standard footprint.

^[4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	100	K/W
	from junction to ambient		<u>[2]</u>	-	-	41	K/W
annoie	ambient		[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

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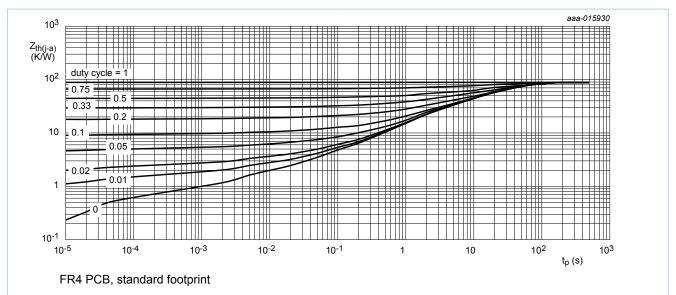


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

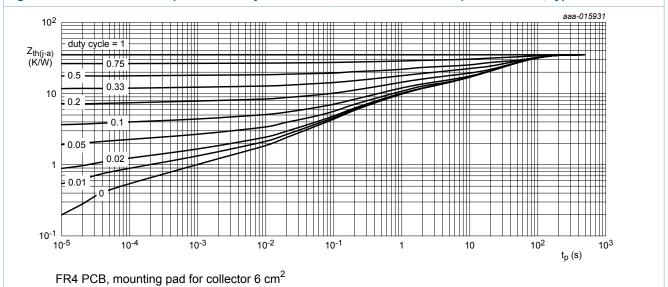


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

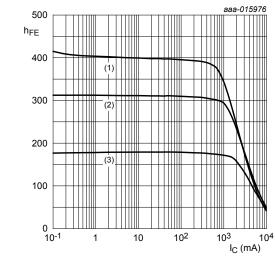
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	150	275	-	
		$V_{CE} = 2 \text{ V}; I_{C} = 1 \text{ A}; t_{p} \le 300 \mu\text{s};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	150	270	-	
		$V_{CE} = 2 \text{ V; } I_{C} = 5 \text{ A; } t_{p} \le 300 \mu\text{s;}$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	60	110	-	
		V_{CE} = 2 V; I_{C} = 10 A; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C; pulsed	25	50	-	
VCEsat	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_{amb} = 25 °C; pulsed	-	30	50	mV
		I_C = 5 A; I_B = 0.5 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	120	180	mV
		I_{C} = 10 A; I_{B} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	250	370	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = 10 \text{ A}; I_B = 1 \text{ A}; t_p \le 300 \text{ µs};$ $\delta \le 0.02; T_{amb} = 25 ^{\circ}C; \text{ pulsed}$	-	25	37	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	0.95	V
		I_C = 5 A; I_B = 0.5 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.15	V
		I_C = 10 A; I_B = 1 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.35	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.5 A; T_{amb} = 25 °C	-	-	0.9	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 5 A; I _{Bon} = 250 mA;	-	25	-	ns
t _r	rise time	I_{Boff} = -250 mA; T_{amb} = 25 °C	-	365	-	ns
t _{on}	turn-on time		-	390	-	ns
t _s	storage time		-	280	-	ns
t _f	fall time		-	220	-	ns
t _{off}	turn-off time		-	500	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	-	145	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	40	70	pF



 $V_{CE} = 2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values

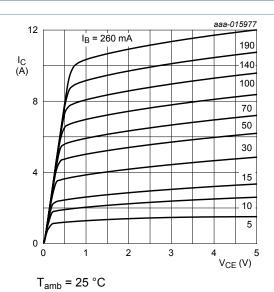
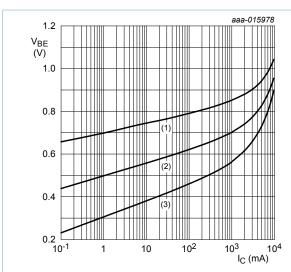


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



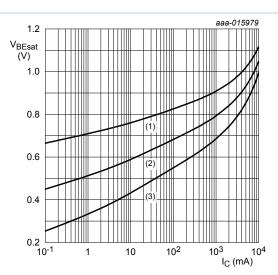
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Base-emitter voltage as a function of collector Fig. 6. current; typical values



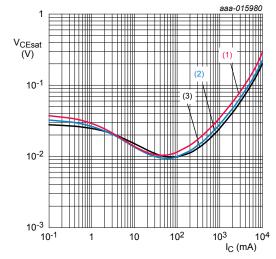
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



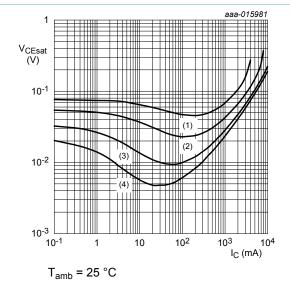
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Collector-emitter saturation voltage as a Fig. 8. function of collector current; typical values



(1)
$$I_C/I_B = 100$$

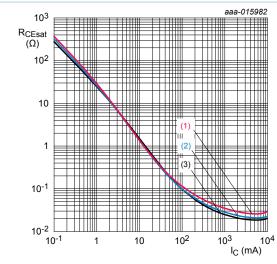
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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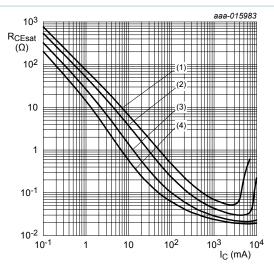
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

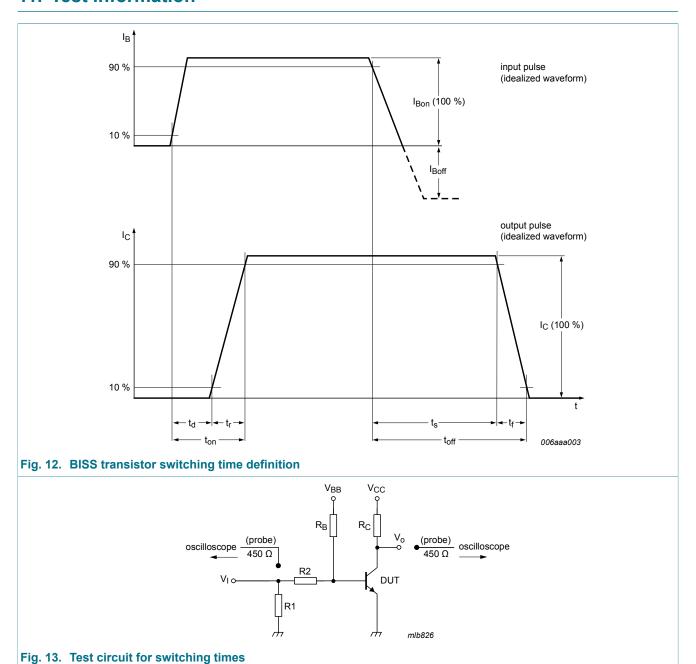
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

(4)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information



11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

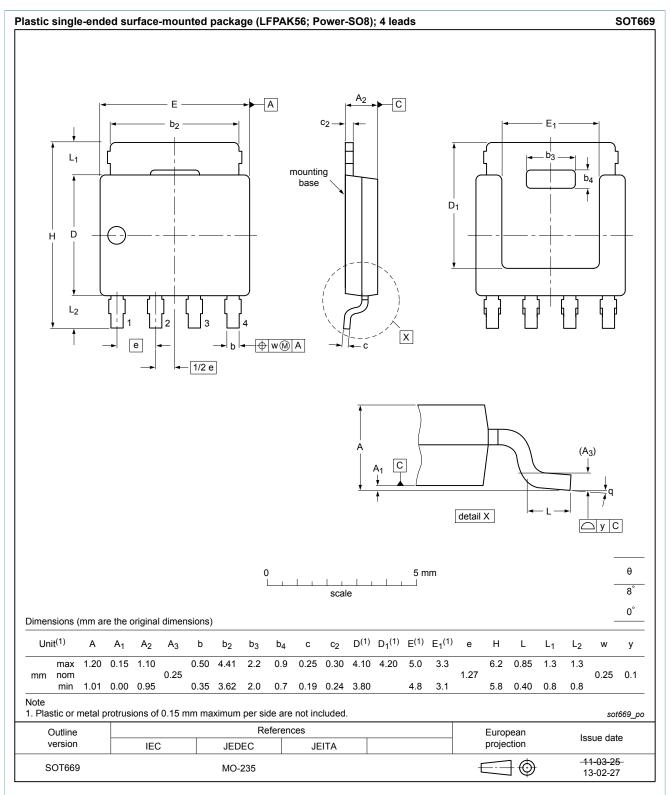
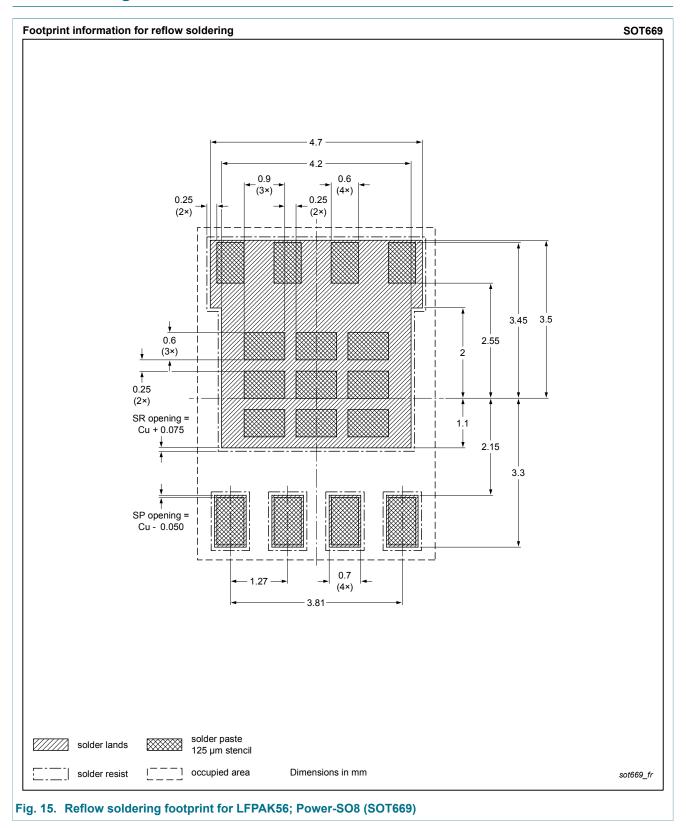


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61010NY v.1	20150320	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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